Supplementary Information: Investigation of Structural and Optoelectronic Properties of Organic Semiconductor Film based on 8-hydroxiquinoline Zinc

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Table SM1. Distances calculated for the hydrogen bridges formed between ZnQ_2 and TCNQ, and HOMO-LUMO gap (E_g).

	B3PW91/6-31G**	PBE/TZ2P
d _{N-Н} (Å)	2.680	2.473
d _{о-н} (Å)	2.337	2.440
E _g (eV)	1.353	0.017

Table SM2. Molecular electronic transitions calculated for ZnQ_2 -TCNQ using TDDFT-PBE/TZ2P method, and the parameters characterizing them: energy electronic transition (E_T), oscillator strength (f), transition from occupied molecular orbital to unoccupied molecular orbital, and weight of the transition.

Dand	Ε _T	Ε _T	f	Molecular Electronic	Weight
Dallu	(nm)	(eV)	(u.a.)	Transition	(%)
с	339.96	3.647	0.040	HOMO \rightarrow LUMO+6	37.6
				HOMO-1 \rightarrow LUMO+5	35.5
	339.68	3.650	0.019	HOMO-1 \rightarrow LUMO+6	39.4
				HOMO \rightarrow LUMO+5	30.7
	289.01	4.290	0.061	HOMO-20 → LUMO	35.1
				HOMO-22 → LUMO	27.4
				HOMO-26 → LUMO	27.8
	273.14	4.539	0.019	HOMO -7 \rightarrow LUMO+1	46.91
				HOMO -8 \rightarrow LUMO+2	36.57
	271.24	4.571	0.212	HOMO-5 \rightarrow LUMO+1	22.5
				HOMO-6 \rightarrow LUMO+2	19.5
Ь				HOMO-8 \rightarrow LUMO+2	13.5
	270.41	4.585	0.185	HOMO-5 \rightarrow LUMO+2	27.9
				HOMO-6 \rightarrow LUMO+1	23.0
	266.34	4.655	0.031	HOMO -9 \rightarrow LUMO+2	54.47
				HOMO -7 \rightarrow LUMO+2	25.02
	265.43	4.671	0.064	HOMO-9 \rightarrow LUMO+1	52.4
				HOMO -7 \rightarrow LUMO+1	21.8
	261.95	4.733	0.028	HOMO -3 \rightarrow LUMO+5	66.83
a	214.10	5.791	0.185	HOMO -3 \rightarrow LUMO+9	61.1
	212.41	5.837	0.126	HOMO -1 \rightarrow LUMO+25	76.0
	209.72	5.912	0.134	HOMO → LUMO+26	33.7
				HOMO -3 → LUMO+11	13.5
	206.71	5.998	0.107	HOMO -43 → LUMO	44.9
				HOMO -3 → LUMO+11	12.9
	206.61 6	6 001	0.126	HOMO -43 → LUMO	50.2
		200.01 0.001		HOMO -3 → LUMO+11	20.9



Figure SM1. Schematization of the main molecular electronic transitions fashioning the bands in the absorption spectrum. Color code: purple arrows represent the transitions in band *a*; blue arrows correspond to transitions in band *b*; and light blue arrows represent the transitions in band *c*.

Ε _T	f	Molecular Electronic		Weight
(eV)	(u.a.)	Transition		(%)
2.393	0.016	HOMO -7 \rightarrow	LUMO	63.3
		HOMO -1 \rightarrow	LUMO+1	18.1
2.434	0.028	HOMO -7 →	LUMO	33.5
		HOMO -1 \rightarrow	LUMO+1	28.4
		HOMO \rightarrow	LUMO+2	26.3
2.636	0.410	HOMO -2 →	LUMO	56.0
		HOMO \rightarrow	LUMO	26.3

Table SM3. Electronic transitions singlet-singlet with energy comparable to the experimental optical gap $E_{opt} = 2.4$ eV, and with a higher probability of occurrence.



Figure SM2. Schematization of the electronic transitions singlet-singlet with energy comparable to the experimental optical gap $E_{opt} = 2.4$ eV, and with a higher probability of occurrence (see table SM3).